

ABSTRACT OF THE DISCLOSURE

A method for manufacturing a semiconductor substrate including a mask aligning trench. The method includes
5 forming the mask aligning trench and an element partitioning trench. The element partitioning and mask aligning trenches are filled with insulation. The insulation in the element partitioning trench is masked and the insulation in the mask aligning trench is etched. As a result, a residue of the
10 insulation in the mask aligning trench is below the upper edge of the mask aligning trench. The mask aligning trench is easily detected. Thus, positioning a patterning mask on the substrate can be performed accurately.